TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74AC367P, TC74AC367F, TC74AC367FN, TC74AC367FT

HEX BUS BUFFER (3 - STATE)

The TC74AC367 is an advanced high speed CMOS HEX BUS BUFFERs fabricated with silicon gate and double - layer metal wiring  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

It contains six buffers; four buffers are controlled by an enable input  $(\overline{G}1)$ , and the other two buffers are controlled by another enable input  $(\overline{G}2)$ . The outputs of each buffer group are enabled when  $\overline{G}1$  and/or  $\overline{G}2$  inputs are held low; if held high, these outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

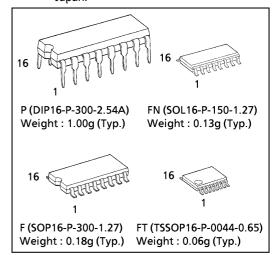
#### FEATURES:

- High Speed-----t<sub>pd</sub> = 3.7ns(typ.) at  $V_{CC}$  = 5V
- Low Power Dissipation ·············· $I_{CC} = 8\mu A(Max.)$ at Ta = 25°C
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Symmetrical Output Impedance···|  $I_{OH}$  | =  $I_{OL}$  = 24mA(Min.)

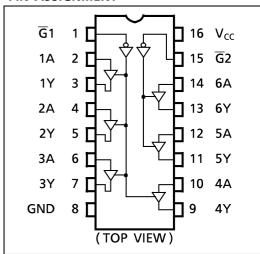
Capability of driving  $50\Omega$  transmission lines.

- Balanced Propagation Delays  $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range ···· V<sub>CC</sub> (opr) = 2V ~ 5.5V
- Pin and Function Compatible with 74F 367

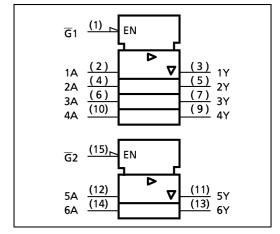
(Note) The JEDEC SOP (FN) is not available in Japan.



#### PIN ASSIGNMENT



## IEC LOGIC SYMBOL



#### TRUTH TABLE

INP	OUTPUTS	
G	Α	Υ
L	L	L
L	Н	Н
Н	Х	Z

X : Don't Care Z : High Impedance

## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	٧
DC Input Voltage	V <sub>IN</sub>	$-0.5 \sim V_{CC} + 0.5$	٧
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	٧
Input Diode Current	I <sub>IK</sub>	± 20	mΑ
Output Diode Current	I <sub>OK</sub>	± 50	mA
DC Output Current	I <sub>OUT</sub>	± 50	mA
DC V <sub>cc</sub> /Ground Current	I <sub>cc</sub>	± 150	mΑ
Power Dissipation	P <sub>D</sub>	500 (DIP)*/ 180 (SOP/TSSOP)	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

\*500mW in the range of Ta =  $-40^{\circ}$ C ~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied up to 300mW.

## **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	2.0~5.5	٧
Input Voltage	VIN	0~V <sub>CC</sub>	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	V
Operating Temperature	Topr	<b>−40~85</b>	°C
Input Rise and Fall Time	dt/dV	$0 \sim 100 \text{ (Vcc} = 3.3 \pm 0.3 \text{V)}$ $0 \sim 20 \text{ (Vcc} = 5 \pm 0.5 \text{V)}$	ns / V

#### DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL		TEST CONDITION		V <sub>cc</sub>	Ta = 25°C			Ta = −40~85°C		UNIT
				(V)	MIN.	TYP.	MAX.	MIN.	MAX.	OIVII
High - Level Input Voltage	V <sub>IH</sub>		2.0 3.0 5.5	1.50 2.10 3.85	_ 	_ _	1.50 2.10 3.85	_ _ _	>	
Low - Level Input Voltage	VIL		2.0 3.0 5.5	_ _ _	111	0.50 0.90 1.65	_ _ _	0.50 0.90 1.65	٧	
High - Level Output Voltage	V	$V_{OH} \qquad V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50\mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	<u> </u>	1.9 2.9 4.4	111	<
	<b>V</b> ОН		$I_{OH} = -4mA$ $I_{OH} = -24mA$ $I_{OH} = -75mA*$	3.0 4.5 5.5	2.58 3.94 —		_ _ _	2.48 3.80 3.85	_ 	V
Low - Level Output Voltage V <sub>OL</sub>	V	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 50 \mu A$	2.0 3.0 4.5	111	0.0 0.0 0.0	0.1 0.1 0.1	_ _ _	0.1 0.1 0.1	v
	VOL		$I_{OL} = 12 \text{mA}$ $I_{OL} = 24 \text{mA}$ $I_{OL} = 75 \text{mA}*$	3.0 4.5 5.5		111	0.36 0.36 —	_ _ _	0.44 0.44 1.65	V
3 - State Output Off - State Current	l <sub>oz</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.5	_	± 5.0	
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GN	5.5	_	_	± 0.1	_	± 1.0	$\mu$ A	
Quiescent Supply Current	I <sub>CC</sub>	$V_{IN} = V_{CC}$ or GN	5.5	_	_	8.0	_	80.0		

<sup>\* :</sup> This spec indicates the capability of driving  $50\Omega$  transmission lines. One output should be tested at a time for a 10ms maximum duration.

# AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50pF, $R_L$ = 500 $\Omega$ , Input $t_r$ = $t_f$ = 3ns )

PARAMETER	CVMPOL	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
FARAIVIETER	SYMBOL		V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>		3.3 ± 0.3 5.0 ± 0.5	_	6.5 4.5	11.0 7.0	1.0 1.0	12.5 8.0	
Output Enable Time	t <sub>pZL</sub> t <sub>pZH</sub>		3.3 ± 0.3 5.0 ± 0.5		7.9 5.5	13.2 8.7	1.0 1.0	15.0 10.0	ns
Output Disable Time	t <sub>pLZ</sub> t <sub>pHZ</sub>		3.3 ± 0.3 5.0 ± 0.5		6.3 5.2	10.5 7.9	1.0 1.0	12.0 9.0	
Input Capacitance	C <sub>IN</sub>			_	5	10	_	10	
Output Capacitance	C <sub>OUT</sub>			_	10	_	_	_	pF
Power Dissipation Capacitance	C <sub>PD</sub> (1)			_	28	_	_	_	

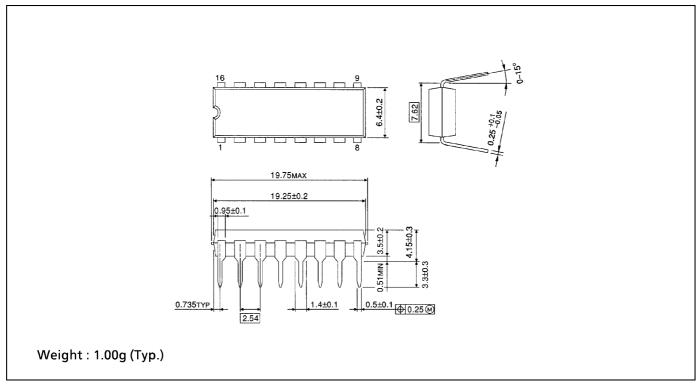
Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(opr.) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 6 (per bit)$$

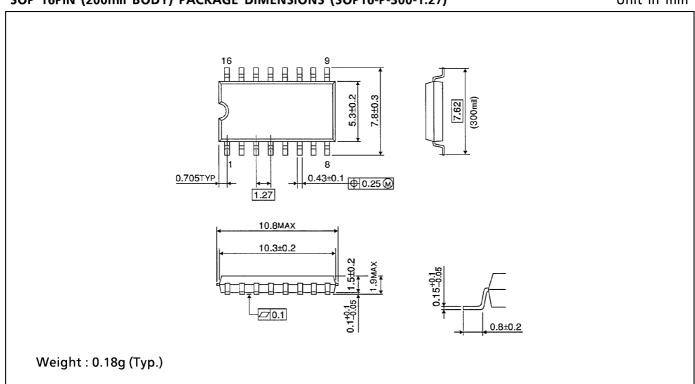
# DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

Unit in mm



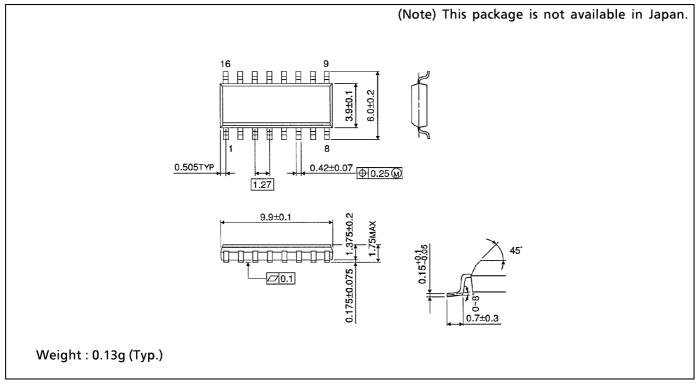
# SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

Unit in mm



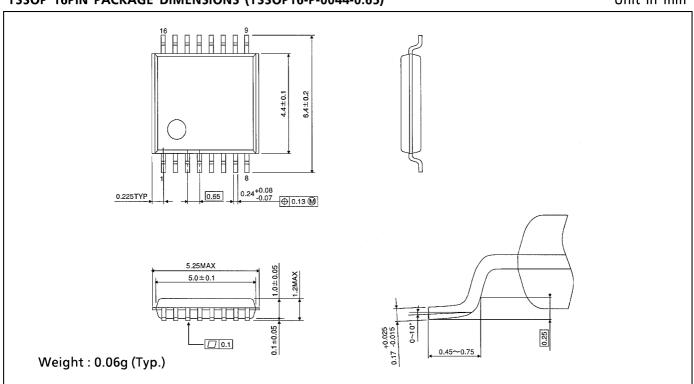
# SOP 16PIN (150mil BODY) PACKAGE DIMENSIONS (SOL16-P-150 -1.27)

Unit in mm



## TSSOP 16PIN PACKAGE DIMENSIONS (TSSOP16-P-0044-0.65)

Unit in mm



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